

MOSFET – Power, Single N-Channel, STD Gate, SO8FL

80 V, 1.9 mΩ, 201 A

NTMFS2D1N08X

Features

- Low QRR, Soft Recovery Body Diode
- Low $R_{DS(on)}$ to Minimize Conduction Losses
- Low QG and Capacitance to Minimize Driver Losses
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

Applications

- Synchronous Rectification (SR) in DC-DC and AC-DC
- Primary Switch in Isolated DC-DC Converter
- Motor Drives

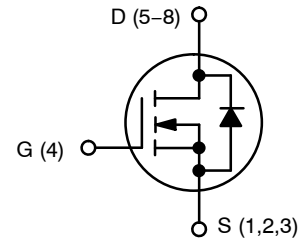
MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise stated)

Parameter	Symbol	Value	Unit	
Drain-to-Source Voltage	V_{DSS}	80	V	
Gate-to-Source Voltage	V_{GS}	± 20	V	
Continuous Drain Current (Note 1)	I_D	$T_C = 25^\circ\text{C}$	201	
		$T_C = 100^\circ\text{C}$	142	
Power Dissipation (Note 1)	P_D	164	W	
Pulsed Drain Current	I_{DM}	$T_C = 25^\circ\text{C}, t_p = 100 \mu\text{s}$	866	
				Pulsed Source Current (Body Diode)
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 to +175	$^\circ\text{C}$	
Source Current (Body Diode)	I_S	248	A	
Single Pulse Avalanche Energy	$I_{PK} = 58 \text{ A}$ (Note 3)	E_{AS}	168	mJ
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)	T_L	260	$^\circ\text{C}$	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

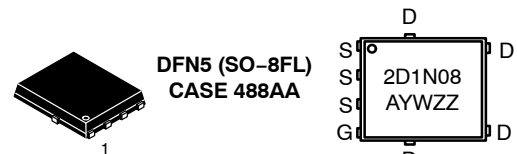
1. The entire application environment impacts the thermal resistance values shown. They are not constants and are only valid for the particular conditions noted.
2. Actual continuous current will be limited by thermal and electromechanical application board design.
3. EAS of 168 mJ is based on started $T_J = 25^\circ\text{C}$, $I_{AS} = 58 \text{ A}$, $V_{DD} = 64 \text{ V}$, $V_{GS} = 10 \text{ V}$, 100% avalanche tested.

$V_{(BR)DSS}$	$R_{DS(ON) MAX}$	$I_D MAX$
80 V	1.9 mΩ @ 10 V	201 A



N-CHANNEL MOSFET

MARKING DIAGRAMS



2D1N08 = Specific Device Code
A = Assembly Location
Y = Year
W = Work Week
ZZ = Lot Traceability

ORDERING INFORMATION

Device	Package	Shipping†
NTMFS2D1N08XT1G	DFN5 (Pb-Free)	1500 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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THERMAL CHARACTERISTICS

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	0.91	°C/W
Thermal Resistance, Junction-to-Ambient (Notes 4 and 5)	$R_{\theta JA}$	39	

4. Surface-mounted on FR4 board using 1 sq-in pad, 1 oz Cu.
 5. $R_{\theta JA}$ is determined by the user's board design.

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = 1\text{ mA}$	80			V
Drain-to-Source Breakdown Voltage (transient)	$\Delta V_{(BR)DSS} / \Delta T_J$	$I_D = 1\text{ mA}$, Referenced to 25°C		31.6		mV/°C
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 80\text{ V}$	$T_J = 25^\circ\text{C}$		1	μA
			$T_J = 125^\circ\text{C}$		250	
Gate-to-Source Leakage Current	I_{GSS}	$V_{GS} = 20\text{ V}, V_{DS} = 0\text{ V}$			100	nA

ON CHARACTERISTICS

Drain-to-Source On Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 50\text{ A}$		1.7	1.9	m Ω
		$V_{GS} = 6\text{ V}, I_D = 25\text{ A}$		2.5	3.8	
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 252\text{ }\mu\text{A}$	2.4		3.6	V
Negative Threshold Temperature Coefficient	$\Delta V_{GS(TH)} / \Delta T_J$	$V_{GS} = V_{DS}, I_D = 252\text{ }\mu\text{A}$,		-7.5		mV/°C
Forward Transconductance	g_{FS}	$V_{DS} = 5\text{ V}, I_D = 50\text{ A}$		158		S

CHARGES AND CAPACITANCES

Input Capacitance	C_{ISS}	$V_{DS} = 40\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$		4470		pF
Output Capacitance	C_{OSS}			1290		
Reverse Transfer Capacitance	C_{RSS}			20		
Output Charge	Q_{OSS}			93		
Total Gate Charge	$Q_{G(TOT)}$	$V_{DD} = 40\text{ V}, I_D = 50\text{ A}, V_{GS} = 6\text{ V}$		39		nC
				63		
Threshold Gate Charge	$Q_{G(TH)}$	$V_{DD} = 40\text{ V}, I_D = 50\text{ A}, V_{GS} = 10\text{ V}$		14		nC
Gate-to-Source Charge	Q_{GS}			21		
Gate-to-Drain Charge	Q_{GD}			10		
Gate Plateau Voltage	V_{GP}			4.7		
Gate Resistance	R_G	$f = 1\text{ MHz}$		0.8		Ω

SWITCHING CHARACTERISTICS

Turn-On Delay Time	$t_{d(ON)}$	Resistive Load, $V_{GS} = 0/10\text{ V}$, $V_{DD} = 40\text{ V}, I_D = 50\text{ A}, R_G = 2.5\text{ }\Omega$		29		ns
Rise Time	t_r			9		
Turn-Off Delay Time	$t_{d(OFF)}$			42		
Fall Time	t_f			7		

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ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified) (continued)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit	
DRAIN-SOURCE DIODE CHARACTERISTICS							
Forward Diode Voltage	V_{SD}	$I_S = 50\text{ A},$ $V_{GS} = 0\text{ V}$	$T_J = 25^\circ\text{C}$		0.82	1.2	V
			$T_J = 125^\circ\text{C}$		0.66		
Reverse Recovery Time	t_{RR}	$V_{GS} = 0\text{ V}, I_S = 50\text{ A},$ $dI_S/dt = 1000\text{ A}/\mu\text{s}, V_{DD} = 40\text{ V}$		26		ns	
Charge Time	t_a			15			
Discharge Time	t_b			11			
Reverse Recovery Charge	Q_{RR}			202			nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

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TYPICAL CHARACTERISTICS

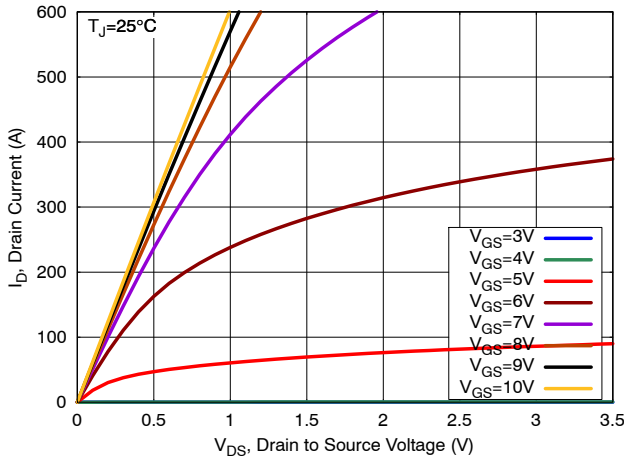


Figure 1. On-Region Characteristics

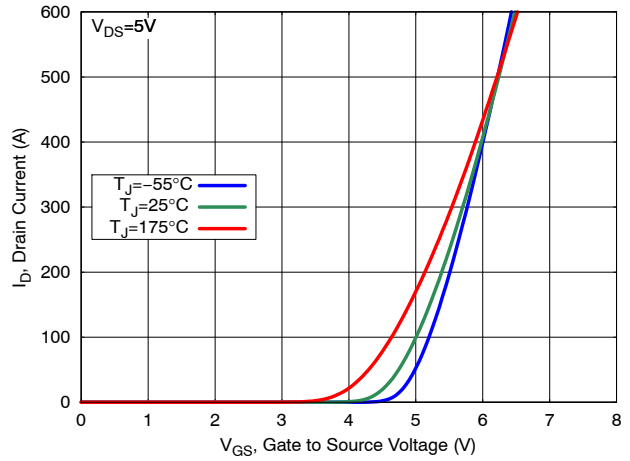


Figure 2. Transfer Characteristics

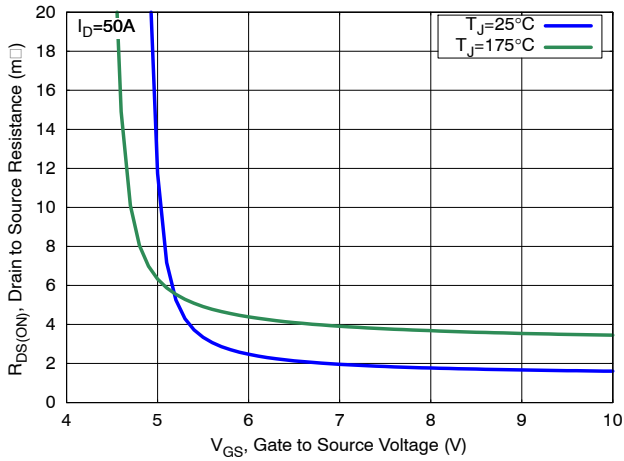


Figure 3. On-Resistance vs. Gate Voltage

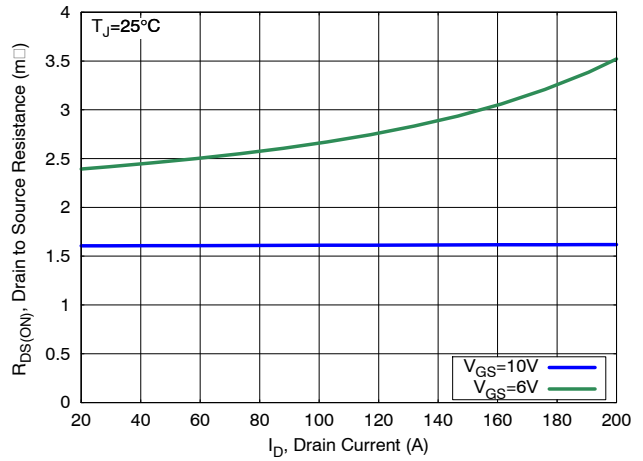


Figure 4. On-Resistance vs. Drain Current

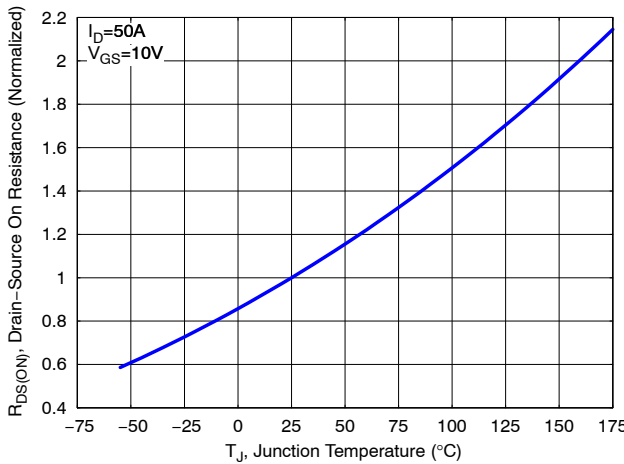


Figure 5. Normalized ON Resistance vs. Junction Temperature

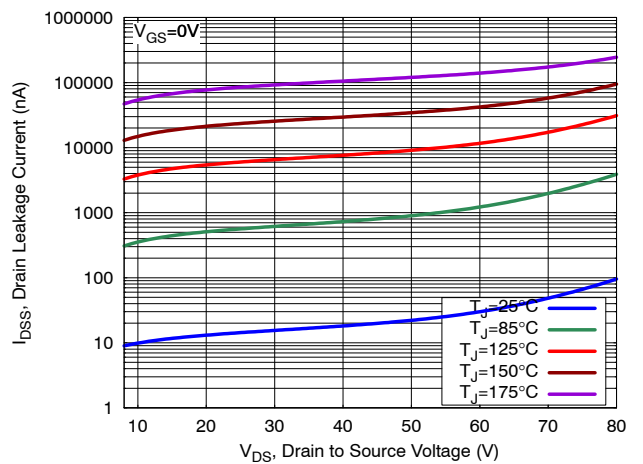


Figure 6. Drain Leakage Current vs. Drain Voltage

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TYPICAL CHARACTERISTICS

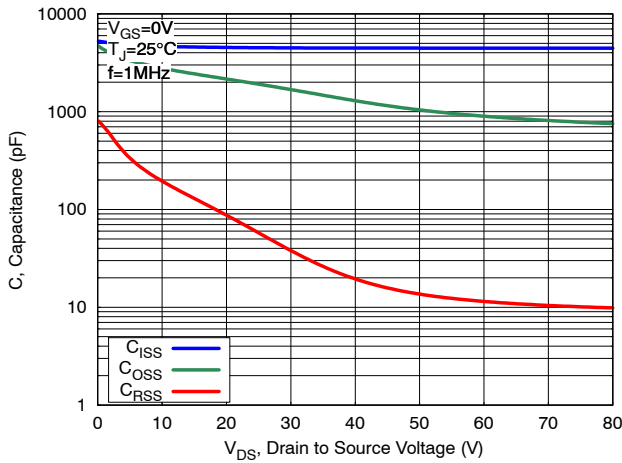


Figure 7. Capacitance Characteristics

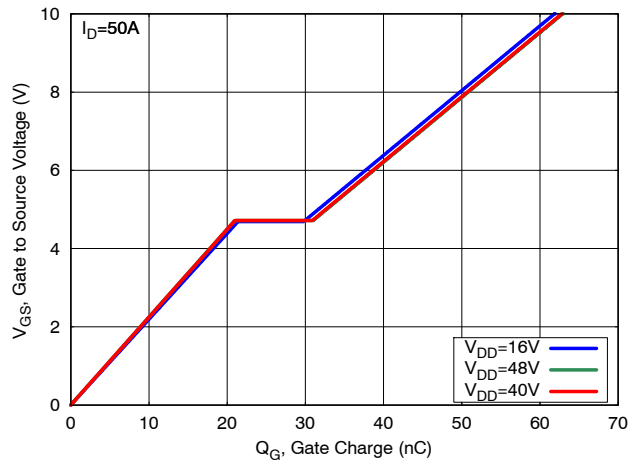


Figure 8. Gate Charge Characteristics

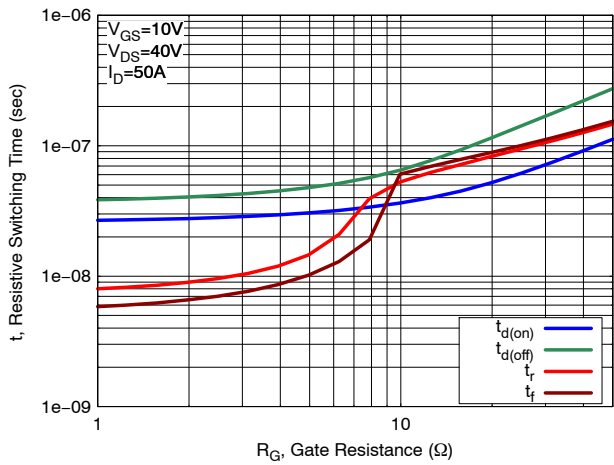


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

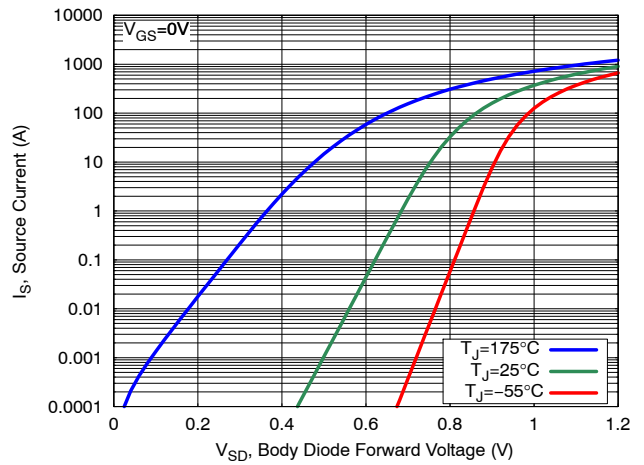


Figure 10. Diode Forward Characteristics

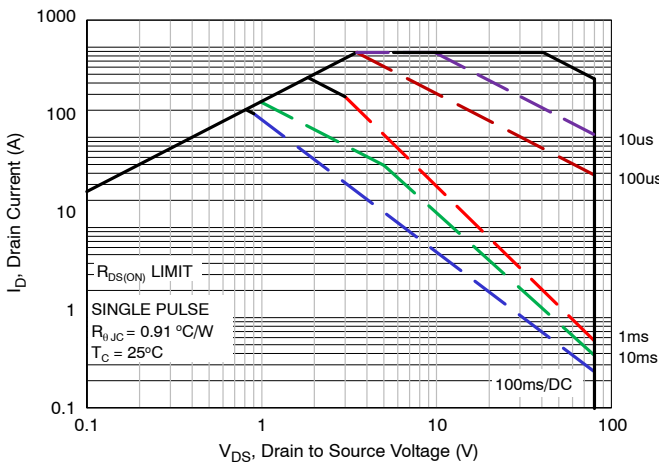


Figure 11. Safe Operating Area (SOA)

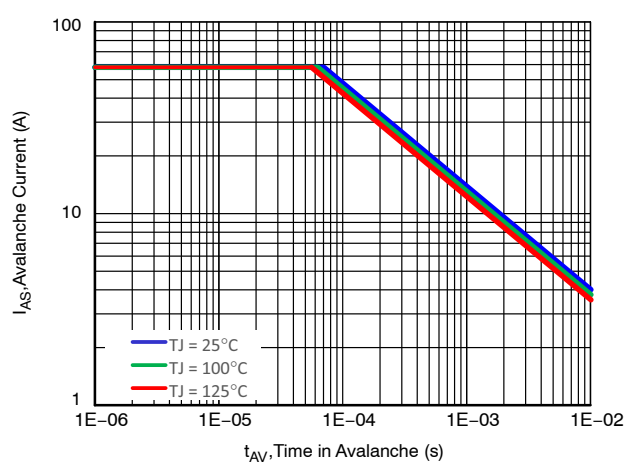


Figure 12. Avalanche Current vs. Pulse Time (UIS)

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TYPICAL CHARACTERISTICS

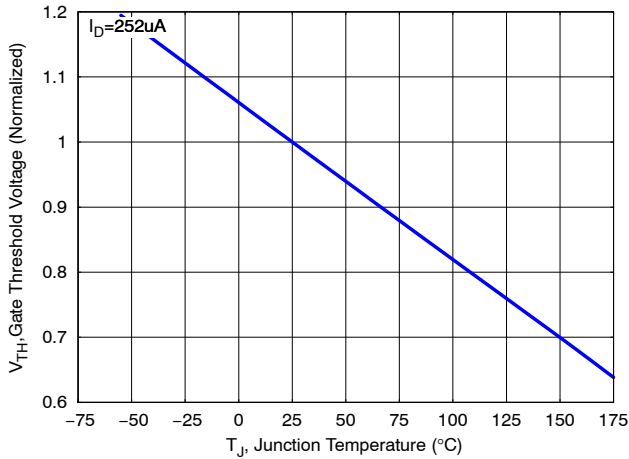


Figure 13. Gate Threshold Voltage vs Junction Temperature

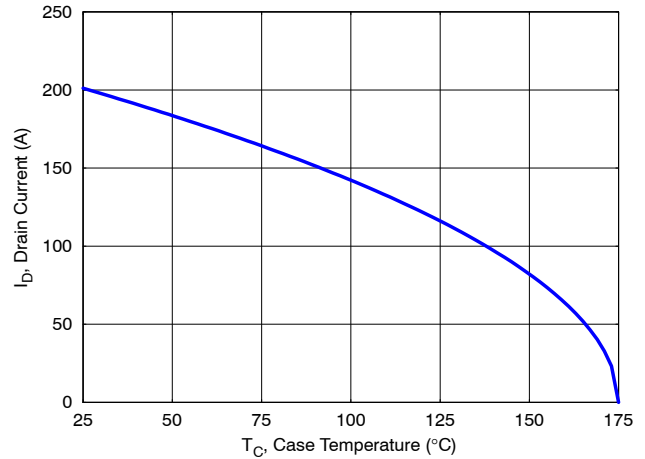


Figure 14. Maximum Current vs. Case Temperature

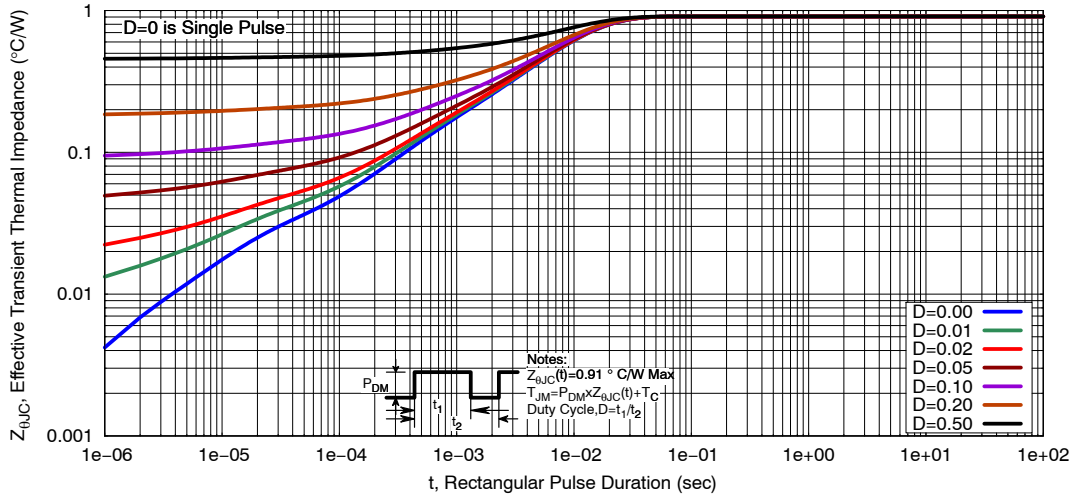
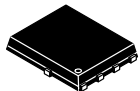


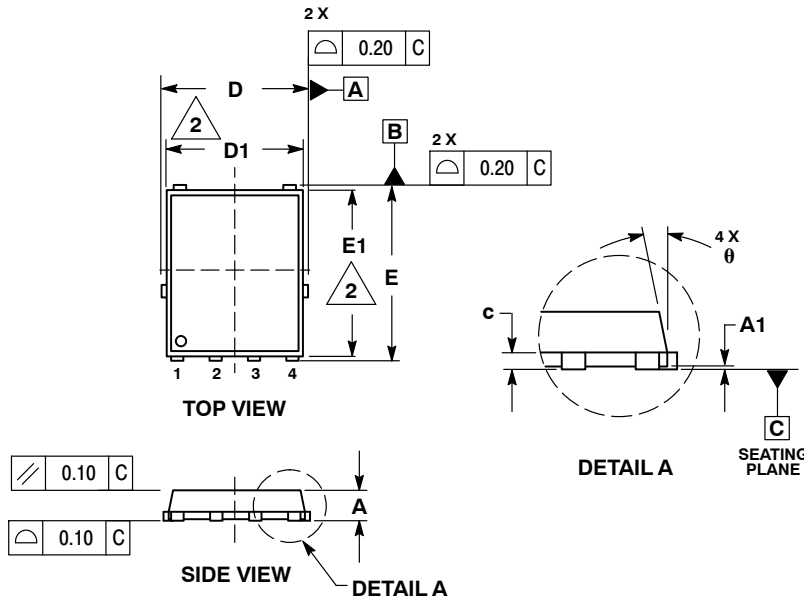
Figure 15. Transient Thermal Response



1
SCALE 2:1

DFN5 5x6, 1.27P
(SO-8FL)
CASE 488AA
ISSUE N

DATE 25 JUN 2018

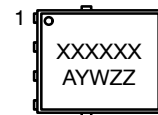


NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION D1 AND E1 DO NOT INCLUDE MOLD FLASH PROTRUSIONS OR GATE BURRS.

DIM	MILLIMETERS		
	MIN	NOM	MAX
A	0.90	1.00	1.10
A1	0.00	---	0.05
b	0.33	0.41	0.51
c	0.23	0.28	0.33
D	5.00	5.15	5.30
D1	4.70	4.90	5.10
D2	3.80	4.00	4.20
E	6.00	6.15	6.30
E1	5.70	5.90	6.10
E2	3.45	3.65	3.85
e	1.27 BSC		
G	0.51	0.575	0.71
K	1.20	1.35	1.50
L	0.51	0.575	0.71
L1	0.125 REF		
M	3.00	3.40	3.80
θ	0°	---	12°

GENERIC MARKING DIAGRAM*



- XXXXXX = Specific Device Code
- A = Assembly Location
- Y = Year
- W = Work Week
- ZZ = Lot Traceability

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.



- STYLE 1:
PIN 1. SOURCE
2. SOURCE
3. SOURCE
4. GATE
5. DRAIN
- STYLE 2:
PIN 1. ANODE
2. ANODE
3. ANODE
4. NO CONNECT
5. CATHODE

*For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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